

## R-C Thermal Model Parameters

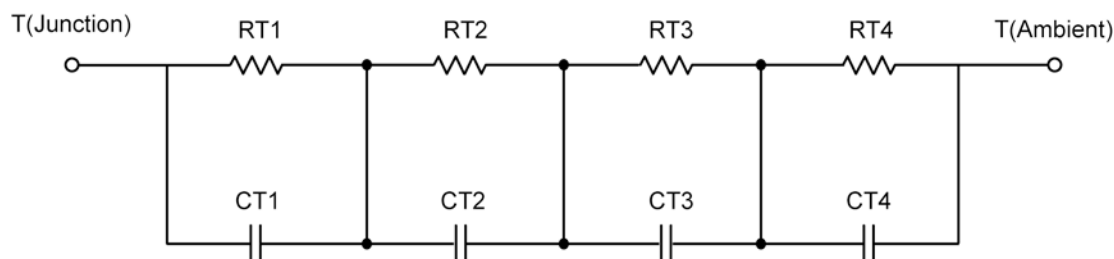
### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*  
For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

### R-C THERMAL MODEL FOR TANK CONFIGURATION

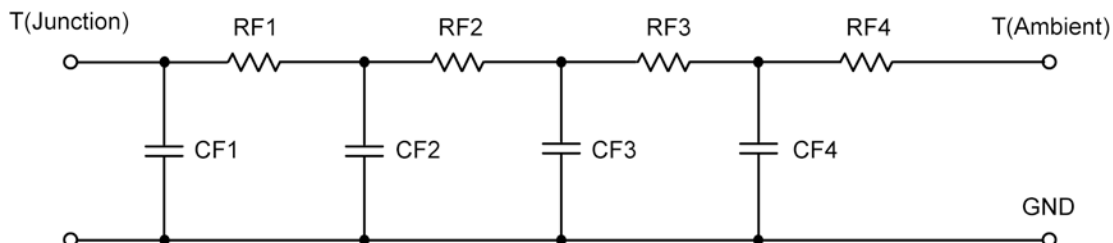


R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	37.7200	193.2446 m	N/A
RT2	3.9719	459.0152 m	N/A
RT3	11.5863	982.0274 m	N/A
RT4	36.7218	165.7128 m	N/A
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	772.8107 m	532.9907 m	N/A
CT2	9.2016 m	1.0329 m	N/A
CT3	172.8203 m	20.0094 m	N/A
CT4	5.9611	1.9611	N/A

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*



## R-C THERMAL MODEL FOR FILTER CONFIGURATION



R-C VALUES FOR FILTER CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RF1	3.8277	502.8130 m	N/A
RF2	17.7865	536.6181 m	N/A
RF3	42.7087	483.1726 m	N/A
RF4	25.6771	277.3963 m	N/A
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CF1	7.3269 m	1.0192 m	N/A
CF2	119.1927 m	14.4969 m	N/A
CF3	658.3181 m	20.2327 m	N/A
CF4	7.8591	441.4775 m	N/A

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

